

### N-channel 30 V 4 m $\Omega$ logic level MOSFET in LFPAK

Rev. 04 — 10 March 2011

**Product data sheet** 

#### 1. Product profile

#### 1.1 General description

Logic level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in industrial and communications applications.

#### 1.2 Features and benefits

- High efficiency due to low switching and conduction losses
- Suitable for logic level gate drive sources

#### **1.3 Applications**

- Class-D amplifiers
- DC-to-DC converters

- Motor control
- Server power supplies

#### 1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	-	30	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 10 V; see <u>Figure 1</u>	-	-	100	A
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	-	69	W
Tj	junction temperature		-55	-	175	°C
Static cha	aracteristics					
$R_{DSon}$	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C	-	2.72	4	mΩ
Dynamic	characteristics					
Q <sub>GD</sub>	gate-drain charge	$V_{GS}$ = 4.5 V; I <sub>D</sub> = 10 A;	-	4.3	-	nC
Q <sub>G(tot)</sub>	total gate charge	V <sub>DS</sub> = 12 V; see <u>Figure 14;</u> see <u>Figure 15</u>	-	17.6	-	nC
Avalanch	e ruggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$\begin{array}{l} V_{GS} = 10 \text{ V}; \ T_{j(\text{init})} = 25 \ ^{\circ}\text{C}; \\ I_{D} = 99 \text{ A}; \ V_{sup} \leq 30 \text{ V}; \\ R_{GS} = 50 \ \Omega; \ \text{unclamped} \end{array}$	-	-	41	mJ

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### 2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source		-
2	S	source	mb	
3	S	source		
4	G	gate	٩ <u>.</u>	
mb	D	mounting base; connected to drain	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	mbb076 S
			SOT669 (LFPAK)	

#### 3. Ordering information

Table 3. Or	dering informatio		
Type number Package			
	Name	Description	Version
PSMN4R0-30	YL LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669

#### 4. Limiting values

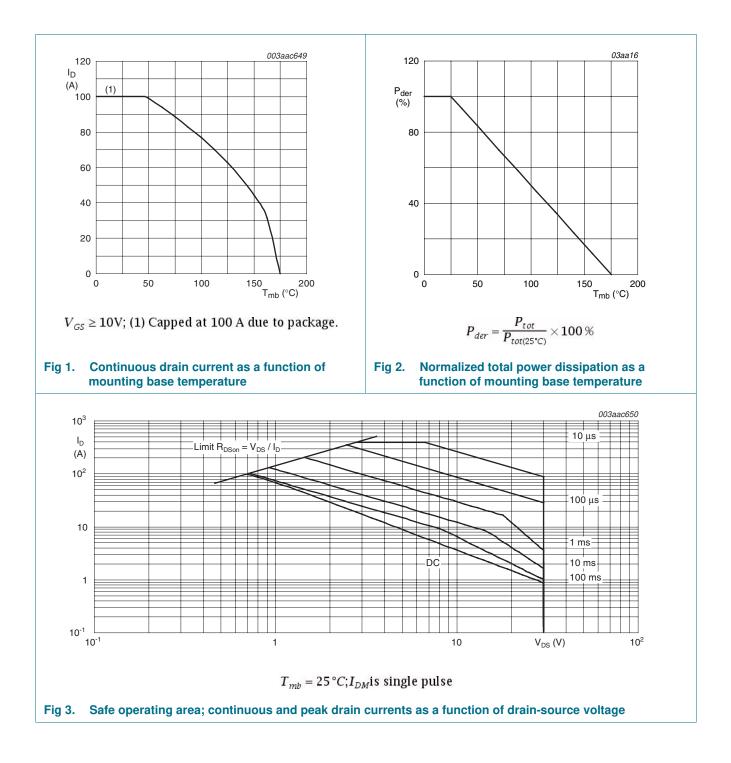
#### Table 4.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C	-	30	V
V <sub>DSM</sub>	peak drain-source voltage	$t_p \le 25 \text{ ns}; f \le 500 \text{ kHz}; E_{DS(AL)} \le 160 \text{ nJ};$ pulsed	-	35	V
V <sub>DGR</sub>	drain-gate voltage	$T_j \ge 25 \text{ °C}; T_j \le 175 \text{ °C}; R_{GS} = 20 \text{ k}\Omega$	-	30	V
V <sub>GS</sub>	gate-source voltage		-20	20	V
I <sub>D</sub>	drain current	$V_{GS}$ = 10 V; $T_{mb}$ = 100 °C; see <u>Figure 1</u>	-	76	А
		$V_{GS}$ = 10 V; $T_{mb}$ = 25 °C; see <u>Figure 1</u>	-	100	А
I <sub>DM</sub>	peak drain current	pulsed; t <sub>p</sub> ≤ 10 µs; T <sub>mb</sub> = 25 °C; see <u>Figure 3</u>	-	396	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; see <u>Figure 2</u>	-	69	W
T <sub>stg</sub>	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drai	n diode				
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	-	99	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$	-	396	А
Avalanche r	uggedness				
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$ \begin{array}{l} V_{GS} = 10 \; V; \; T_{j(\text{init})} = 25 \; ^{\circ}\text{C}; \; I_{D} = 99 \; \text{A}; \\ V_{sup} \leq 30 \; V; \; R_{GS} = 50 \; \Omega; \; unclamped \end{array} $	-	41	mJ

## PSMN4R0-30YL

#### N-channel 30 V 4 m $\Omega$ logic level MOSFET in LFPAK



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#### 5. Thermal characteristics

#### Table 5. **Thermal characteristics** Symbol Parameter Conditions Min Тур Мах Unit thermal resistance from junction to see Figure 4 1 1.82 K/W R<sub>th(j-mb)</sub> \_ mounting base 003aac648 10 Z<sub>th(j-mb)</sub> (K/W) $\delta = 0.5$ 1 ŦĦ 0.2 +++ +++ 0.1 0.05 Ρ tp δ= 10<sup>-1</sup> 0.02 t<sub>o</sub>|single shot т 10<sup>-2</sup> 1

10<sup>-3</sup>

10<sup>-2</sup>

10<sup>-1</sup>

t<sub>p</sub> (s)

1

#### Fig 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

10<sup>-4</sup>

10<sup>-6</sup>

10<sup>-5</sup>

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### 6. Characteristics

#### Table 6. Characteristics

Tested to JEDEC standards where applicable.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	cteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown	$I_D = 250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^\circ C$	30	-	-	V
	voltage	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ\text{C}$	27	-	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 11</u> ; see <u>Figure 12</u>	1.3	1.7	2.15	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 150 \text{ °C};$ see <u>Figure 12</u>	0.65	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ see <u>Figure 12</u>	-	-	2.45	V
I <sub>DSS</sub>	drain leakage current	$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	1	μA
		$V_{DS} = 30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	100	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 16 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
		$V_{GS}$ = -16 V; $V_{DS}$ = 0 V; $T_j$ = 25 °C	-	-	100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS} = 4.5 \text{ V}; I_D = 15 \text{ A}; T_j = 25 \text{ °C}$	-	3.73	5.25	mΩ
	resistance	$V_{GS}$ = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 150 °C; see <u>Figure 13</u>	-	-	7	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 15 A; T <sub>j</sub> = 25 °C	-	2.72	4	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz	-	0.52	1.5	Ω
Dynamic cha	aracteristics					
Q <sub>G(tot)</sub>	total gate charge	$I_D$ = 10 A; $V_{DS}$ = 12 V; $V_{GS}$ = 10 V; see <u>Figure 14</u> ; see <u>Figure 15</u>	-	36.6	-	nC
		$I_D = 10 \text{ A}; V_{DS} = 12 \text{ V}; V_{GS} = 4.5 \text{ V};$ see <u>Figure 14</u> ; see <u>Figure 15</u>	-	17.6	-	nC
		$I_D = 0 \text{ A}; V_{DS} = 0 \text{ V}; V_{GS} = 10 \text{ V}$	-	33	-	nC
Q <sub>GS</sub>	gate-source charge	$I_D = 10 \text{ A}; V_{DS} = 12 \text{ V}; V_{GS} = 4.5 \text{ V};$	-	5.6	-	nC
Q <sub>GS(th)</sub>	pre-threshold gate-source charge	see <u>Figure 14;</u> see <u>Figure 15</u>	-	3.6	-	nC
Q <sub>GS(th-pl)</sub>	post-threshold gate-source charge		-	2	-	nC
Q <sub>GD</sub>	gate-drain charge		-	4.3	-	nC
V <sub>GS(pl)</sub>	gate-source plateau voltage	V <sub>DS</sub> = 12 V; see <u>Figure 14;</u> see <u>Figure 15</u>	-	2.3	-	V
C <sub>iss</sub>	input capacitance	$V_{DS} = 12 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$	-	2090	-	pF
C <sub>oss</sub>	output capacitance	$T_j = 25 \text{ °C}; \text{ see } Figure 16$	-	469	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	227	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS} = 12 \; V; \; R_L = 0.5 \; \Omega; \; V_{GS} = 4.5 \; V; \;$	-	28	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 4.7 \Omega$	-	51	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	44	-	ns
t <sub>f</sub>	fall time		-	18	-	ns

Table 6.

Symbol

V<sub>SD</sub>

Source-drain diode

Characteristics ... continued

Tested to JEDEC standards where applicable.

source-drain voltage

Parameter

## PSMN4R0-30YL

Typ

0.83

Max

1.2

Unit

V

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Min

#### see Figure 17 $\label{eq:IS} \begin{array}{l} I_S = 20 \text{ A}; \mbox{d} I_S/\mbox{d} t = -100 \text{ A}/\mbox{\mu} s; \\ V_{GS} = 0 \text{ V}; \mbox{V}_{DS} = 20 \text{ V} \end{array}$ t<sub>rr</sub> reverse recovery time 39 -\_ ns recovered charge 36 nC Qr --*003aac639* 003aac641 80 120 $\mathbf{I}_{\mathsf{D}}$ $I_D$ 10 $V_{GS}(V) = 3.2$ (A) (A) 100 60 3 80 2.8 40 60 T<sub>i</sub> = 150 °C 40 2.6 20 25 <sup>6</sup>C 20 2.4 2.2 0 0 8 10 V<sub>DS</sub> (V) Λ 1 2 3 V<sub>GS</sub> (V) 4 0 2 4 6 $V_{DS} = 10V$ $T_{i} = 25 \,^{\circ}C; t_{p} = 300 \,\mu s$ Transfer characteristics: drain current as a Output characteristics: drain current as a Fig 5. Fia 6. function of gate-source voltage; typical values function of drain-source voltage; typical values 003aac644 003aac642 10 100 g<sub>fs</sub> R<sub>DSon</sub> (S) $(m\Omega)$ 80 8 $V_{GS}(V) = 3.2$ 60 6 40 45 4 20 10 2 0 0 20 40 60 0 20 40 60 80 <sub>ID</sub> (A) 100 $I_D(A)$ $T_j = 25 \,^{\circ}C; V_{DS} = 15V$ $T_j = 25 \,^{\circ}C; t_p = 300 \,\mu s$ Drain-source on-state resistance as a function Forward transconductance as a function of Fig 7. Fig 8. of drain current; typical values drain current; typical values

Conditions

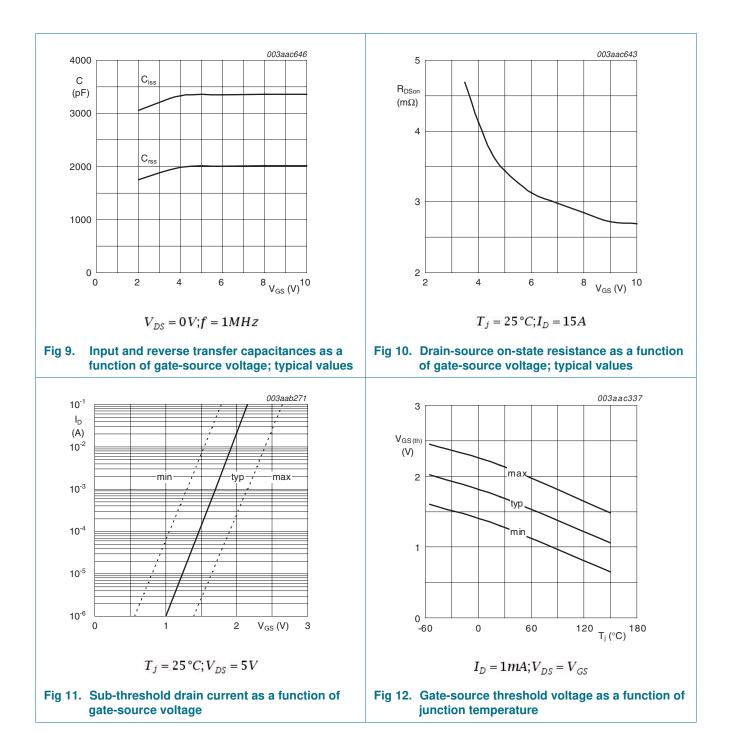
 $I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ 

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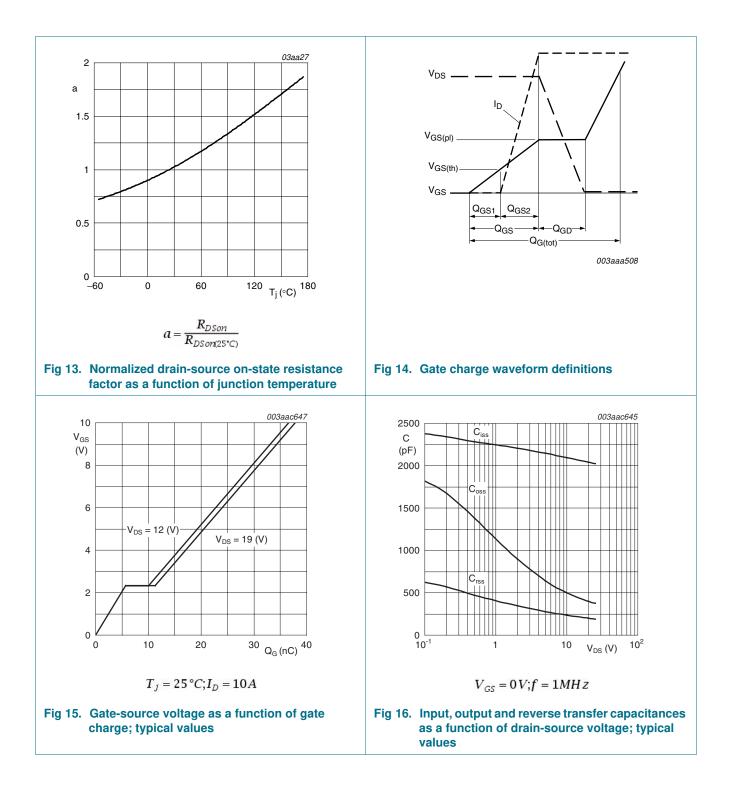
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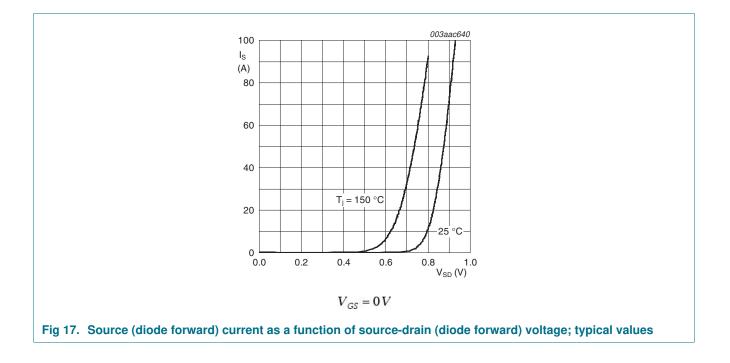
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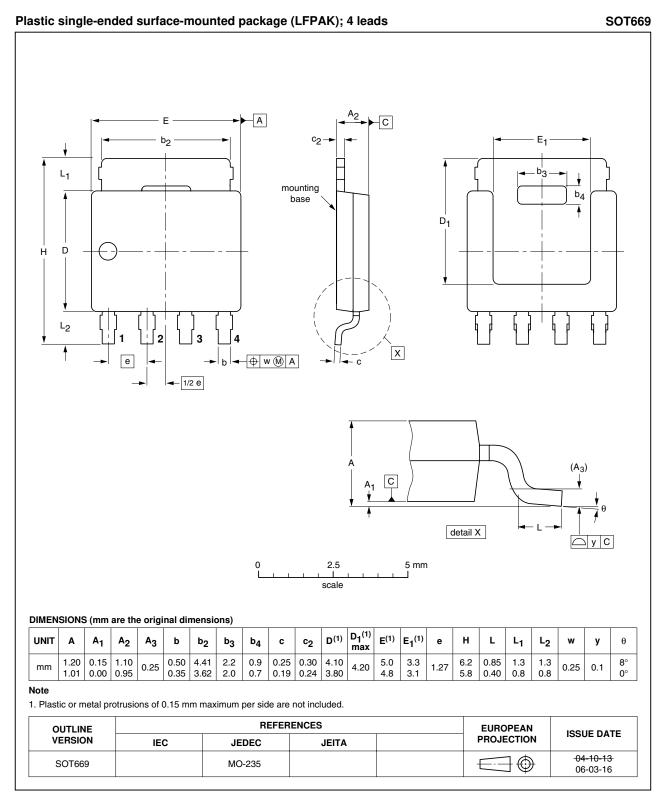
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#### N-channel 30 V 4 mΩ logic level MOSFET in LFPAK



N-channel 30 V 4 m $\Omega$  logic level MOSFET in LFPAK

#### 7. Package outline



#### Fig 18. Package outline SOT669 (LFPAK)

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#### N-channel 30 V 4 mΩ logic level MOSFET in LFPAK

### 8. Revision history

#### Table 7.Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
PSMN4R0-30YL v.4	20110310	Product data sheet	-	PSMN4R0-30YL v.3	
Modifications:	Various changes	to content.			
PSMN4R0-30YL v.3	20091231	Product data sheet	-	PSMN4R0-30YL v.2	

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#### 9. Legal information

#### 9.1 Data sheet status

Document status [1] [2]	Product status 3	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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